DC characteristics of InAs/AlSb HEMTs at cryogenic temperatures

G. Moschetti, P-Å Nilsson, N. Wadefalk, M. Malmkvist, E. Lefebvre, J. Grahn
Microwave Electronics Laboratory, Department of Microtechnology and Nanoscience (MC2)
Chalmers University of Technology, SE-412 96 Göteborg, Sweden

Y. Roelens, A. Noudeviwa, A. Olivier, S. Bollaert, F. Danneville, L. Desplanque, X. Wallart, G. Dambrine
Institute of Electronics, Microelectronics and Nanotechnology, IEMN / CNRS UMR 8520
University of Lille – Av. Poincaré, 59652 Villeneuve d'Ascq, France

Abstract

The DC properties of 110-nm gate-length InAs/AlSb-based HEMTs at cryogenic (30K) and room temperature (300K) have been investigated. Compared to 300K, devices at 30 K exhibited lower on-resistance ($R_{ON}$) and output conductance ($g_{DS}$), a higher transconductance ($g_m$) and a more distinct knee in the $I_{DS}(V_{DS})$ characteristics. The improvement in the DC performance at cryogenic temperature should mainly be attributed to the lower source-drain resistance.

I. Introduction

InAs/AlSb HEMTs are characterized by higher electron mobility and peak velocity in the active channel layer compared to InGaAs/InAlAs HEMTs [1]. Such characteristics make InAs/AlSb HEMTs potentially interesting in millimetre-wave applications e.g. space communication systems and radio astronomy where low power dissipation and low noise figure are required. Since the signal amplitude in long range space communication is extremely weak, it is necessary to reduce the noise contribution of the receiver by cryogenic cooling of the low-noise amplifier.

The DC and RF performance are sensitive to the operating temperature, especially in 2DEG based devices, due to the contact resistance, electron transport improvements and reduction of thermal noise. Very little has been reported on cryogenic device properties in InAs/AlSb HEMTs [2]. In this paper we have studied the DC performance at cryogenic temperature by measuring InAs/AlSb based HEMTs at 300 K and 30 K.

II. Experiment

The InAs/AlSb HEMT fabrication started with a heterostructure grown by molecular beam epitaxy on a semi-insulating InP substrate. The heterostructure is shown in Fig. 1. Mesa isolation was performed by Cl₂:Ar ICP/RIE dry etching. Pt/Pd/Au ohmic contacts were then deposited and subsequently annealed at 275°C.

The Ti/Pt/Au T-shaped gates with gate length $L_g = 110$ nm were defined in a two-layer resist by electron beam lithography.

The 5 nm deep gate-recess etch was performed by a citric-acid based wet etchant prior to gate metallization. Finally, a SiN passivation layer was deposited to protect the devices and an ICP/RIE dry etching step was used to expose the metallic pads. DC measurements were then performed.
The effective gate-to-channel distance of 20 nm is defined as the total thickness of the Schottky layer, protection layer, the spacer thickness including a doping layer of approximately 1 nm. Transmission line model (TLM) test structures characterization was carried out at room temperature to evaluate the contact resistance \( R_c \) and the sheet resistance \( R_{sh} \). The values obtained were 0.07 \( \Omega \) mm and 108 \( \Omega / \square \), respectively.

III. Results and discussion

The device reported here is a two finger HEMT with a total gate width of 100 \( \mu \)m. All the measurements at both room temperature (300 K) and cryogenic temperature (30 K) were performed on the same device. The drain current as a function of drain voltage was first measured at 300 K; See Fig. 2. The on-resistance observed was about 0.5 \( \Omega \) mm. The \( f_t \) and \( f_{max} \) was 190 GHz and 170 GHz, respectively. These values represent typical state-of-the-art [3] numbers for an InAs/AlSb HEMT with \( L_g=110 \) nm. The DC measurements were carried out at 30 K using a cryogenic probe station. At this temperature, the observed device behaviour was clearly different showing a lower \( R_{ON} \) (about 0.3 \( \Omega \) mm ) and higher \( I_{DS} \) at low \( V_{DS} \). See Fig. 2. This behaviour is mainly due to the reduction of the source-drain resistance. In particular, the output conductance \( g_{DS} \) was reduced at low \( V_{DS} \) and high \( I_{DS} \). Furthermore, the device developed a more distinct knee in the \( I_{DS} \) versus \( V_{DS} \) with no observed kink behaviour.

In Fig. 3 the transconductance at both 300 K and 30 K is shown. The drain voltage \( V_{DS} \) was varied from 0 V to 0.5 V. The measurement at 300 K showed a maximum peak \( g_m \) of about 950 mS/mm at \( V_{GS} \approx 1.1 \) V and \( V_{DS} \approx 0.5 \) V. When the same measurement was repeated at 30 K, an increased peak transconductance \( g_m \) of 1280 mS/mm was observed. The \( g_m \) curve was also slightly shifted towards higher negative gate bias. Higher \( g_m \) indicates a better gate control of the current and a possible increment of the average carrier velocity. This enhancement in peak \( g_m \) at 30 K can then be attributed not only to the lower source-drain resistance but possibly also to the lower transit time under the gate because of phonon scattering suppression compared with the 300 K values [4].

The maximum gate leakage current \( I_{GS} \) measured at 300 K was 900 \( \mu \)A (9 mA/mm) for \( V_{GS} = -1.4 \) V; See Fig. 4. The same measurement performed at 30 K shows a lower gate leakage of 400 \( \mu \)A (4 mA/mm) for \( V_{GS} = -1.4 \) V. The overall improvement could be explained by a lower impact ionization effect at high negative gate bias above 1 V. The improved DC properties of InAs/AlSb HEMTs at 30 K compared to 300 K points to the potential of this technology in cryogenic low-
noise amplifier applications operating at low DC power dissipation.

A scanning electron microscopy (SEM) image of the two finger InAs/AlSb HEMT is shown in figure 5.

![Fig. 5: SEM image showing the 2x50μm InAs/AlSb HEMT.](image)

III. Conclusions

We have demonstrated that the DC performance for a 110-nm gate-length InAs/AlSb HEMT is clearly improved at cryogenic temperature compared to room temperature. In particular, the on-resistance decreased from about 0.5 Ωmm to about 0.3 Ωmm due to the lower source-drain resistance and the maximum transconductance increased from 950 mS/mm to 1280 mS/mm. The output conductance $g_{DS}$ was reduced especially at low $V_{DS}$, and the device developed a more distinct knee in the $I_D$ versus $V_{DS}$ with no observed kink behaviour. This should also improve the RF performance of InAs/AlSb HEMTs and make them potential device candidates for cryogenic low-noise amplifiers.

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References


